

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	294298	semiconductor and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:05
L2	114014	1 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:05
L3	40073	2 and source and drain and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:06
L4	9	3 and (contradop\$3 or (contra adj dop\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:06

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(method and program\$3 and drain and source and channel and contradop\$3 and direct\$2).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:00
L2	0	(memory and program\$3 and source and drain and channel and contradop\$3 and direct\$2 and concentration).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:02

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(method and program\$3 and drain and source and channel and (contra adj dop\$3) and direct\$2).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:39
L2	0	(memory and program\$3 and source and drain and channel and (contra adj dop\$3) and direct\$2 and concentration).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 15:40